

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10727746
	Filing Date		2003-12-03
	First Named Inventor	Heng Liu	
	Art Unit	1792	
	Examiner Name	Ram N. Kackar	
	Attorney Docket Number	M-15626-1D US	

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	1	J. DAI "Atmospheric pressure MOCVD Growth of high-quality ZnO films on A1 O templates", Journal of Crystal Growth 283 (2005), pp. 93-99	<input type="checkbox"/>
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